

CLAIMS

1. A ceramic heater, for a semiconductor producing/examining device, comprising a ceramic substrate and a resistance heating element formed on a surface thereof,

wherein a gutter is formed along the direction of current flowing through the resistance heating element.

2. The ceramic heater for a semiconductor producing/examining device according to claim 1,

wherein said gutter has a depth of 20% or more of the thickness of the resistance heating element.

3. The ceramic heater for a semiconductor producing/examining device according to claim 1 or 2,

wherein a resistance value scattering in said resistance heating element to the average resistance value of said resistance heating element is 5% or less.

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